

TECHNICAL DATA
DATA SHEET 1004, REV. A
Formerly part number SHDG1025

# 1200 VOLT, 35 AMP IGBT DEVICE

## HIGH SPEED, IMPROVED SCSOA WITH FAST REVERSE RECOVERY DIODE

### **ELECTRICAL CHARACTERISTICS**

(Tj=25°C UNLESS OTHERWISE SPECIFIED)

ELECTRICAL CHARACTERISTICS			(TJ=25°C UNLESS OTHERWISE SPECIFIED)					
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT			
IGBT SPECIFICATIONS								
Collector to Emitter Breakdown Voltage	BV <sub>CES</sub>	-	-	1200	V			
$I_C = 250 \mu A, V_{GE} = 0V$								
Continuous Collector Current $T_C = 25$ $^{\circ}$ C	Ic	-	-	40 (1)	Α			
$T_C = 90$ $^{\circ}C$				35				
Gate to Emitter Voltage	$V_{GE}$	-	-	+/-20	V			
Gate-Emitter Leakage Current I <sub>GE</sub> = +/-20V	I <sub>GES</sub>	-	-	+/-500	nA			
Gate Threshold Voltage, I <sub>C</sub> =2mA	V <sub>GE(TH)</sub>	4.5	6.0	7.5	V			
Zero Gate Voltage Collector Current	I <sub>CES</sub>	-	-	1000	μΑ			
$V_{GE}=0V V_{CE}=1200 V, T_{i}=25^{\circ}C$				5.0	<b></b> ∧			
$V_{CE} = 800 \text{ V}, T_i = 125^{\circ}\text{C}$					mA			
Collector to Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	-	2.7	3.3	V			
$I_C = 35A, V_{GE} = 15V$	02(0,11)							
Input Capacitance	C <sub>ies</sub>	-	8400	-	pF			
Output Capacitance	C <sub>oes</sub>		350					
Reverse Transfer Cap. $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	C <sub>res</sub>		90					
Turn On Delay Time	t <sub>d(on)</sub>	-	90	-				
Rise Time	t <sub>r</sub> `	_	50	_	nsec			
Turn Off Delay Time	t <sub>d(off)</sub>	_	270	_				
Fall Time Turn-off Energy Loss	t <sub>f</sub>		80					
Turn-on Energy Loss	E <sub>off</sub>	_	4.7	_	mJ			
$(I_C = 30A, V_{GE} = 15V, V_{CE} = 600 V, R_G = 5 \Omega$	E <sub>on</sub>	-	5.5	-	mJ			
Junction-to-Case Thermal Resistance	$R_{ heta JC}$	-	-	0.35	°C/W			

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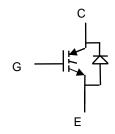
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#### **ULTRAFAST DIODE RATINGS AND CHARACTERISTICS**

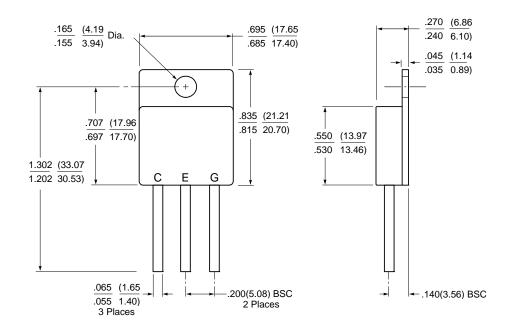
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Diode Peak Inverse Voltage	PIV	-	-	1200	V
Diode Forward Voltage $I_{EC} = 25A$	V <sub>EC</sub>	-	1.9	2.4	V
Diode Reverse Recovery Time (I <sub>F</sub> =20A,di/dt 200 A/μs)	t <sub>rr</sub>	-	-	150	nsec
Maximum Thermal Resistance	R <sub>θJC</sub>	-	-	1.0	°C/W
Operating Junction Temperature	T <sub>jmax</sub>	-55	-	150	°C/W

<sup>(1)</sup> Current is limited by package leads. Die current rating is 70A.

**Schematic Diagram:** 



# Package Drawing: (TO258)



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